

Part Number: TA12-41SEKWB

Super Bright Orange

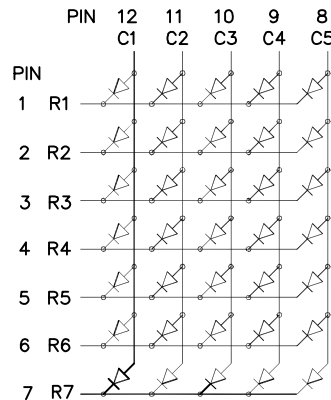
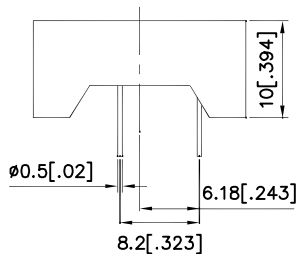
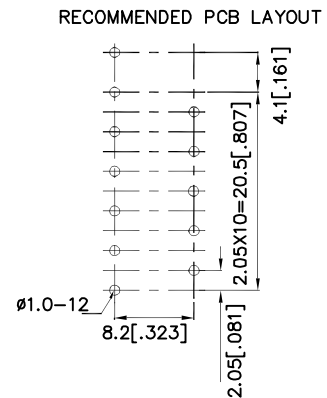
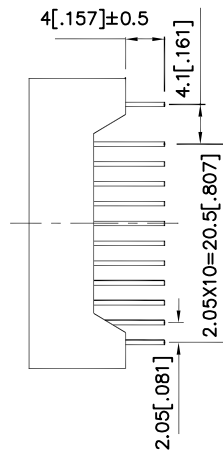
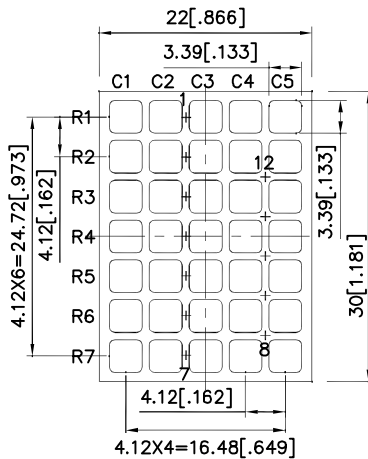
Features

- 1.107 inch matrix height.
- Low current operation.
- High contrast and light output.
- Easy mounting on P.C. boards or sockets.
- Categorized for luminous intensity.
- Mechanically rugged.
- RoHS compliant.

Description

The Super Bright Orange device is made with AlGaInP (on GaAs substrate) light emitting diode chip.

Package Dimensions & Internal Circuit Diagram



Notes:

1. All dimensions are in millimeters (inches), Tolerance is ±0.25(0.01") unless otherwise noted.
2. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.

Selection Guide

Part No.	Dice	Lens Type	Iv (ucd) [1] @ 10mA		Description
			Min.	Typ.	
TA12-41SEKWB	Super Bright Orange (AlGaInP)	White Diffused	88000	240000	Column Anode

Note:

1. Luminous intensity/ luminous Flux: +/-15%.

Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
λ_{peak}	Peak Wavelength	Super Bright Orange	610		nm	I _F =20mA
λ_D [1]	Dominant Wavelength	Super Bright Orange	601		nm	I _F =20mA
$\Delta\lambda_{1/2}$	Spectral Line Half-width	Super Bright Orange	29		nm	I _F =20mA
C	Capacitance	Super Bright Orange	15		pF	V _F =0V;f=1MHz
V _F [2]	Forward Voltage	Super Bright Orange	2.1	2.5	V	I _F =20mA
I _R	Reverse Current	Super Bright Orange		10	uA	V _R =5V

Notes:

1. Wavelength: +/-1nm.
2. Forward Voltage: +/-0.1V.

Absolute Maximum Ratings at TA=25°C

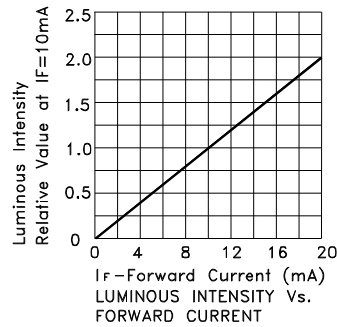
Parameter	Super Bright Orange	Units
Power dissipation	75	mW
DC Forward Current	30	mA
Peak Forward Current [1]	195	mA
Reverse Voltage	5	V
Operating / Storage Temperature	-40°C To +85°C	
Lead Solder Temperature[2]	260°C For 3-5 Seconds	

Notes:

1. 1/10 Duty Cycle, 0.1ms Pulse Width.
2. 2mm below package base.



Super Bright Orange TA12-41SEKWB



PACKING & LABEL SPECIFICATIONS

TA12-41SEKWB

